

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The ASI ASAT10 is Designed for

**FEATURES:**

- Input Matching Network
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	2.3 A
<b>V<sub>CB0</sub></b>	45 V
<b>V<sub>CEO</sub></b>	15 V
<b>V<sub>EBO</sub></b>	3.5 V
<b>P<sub>DISS</sub></b>	29 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	6.0 °C/W

**PACKAGE STYLE .250 2L FLG(A)**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.055 / 1.40	.065 / 1.65
B	.124 / 3.15	
C	.243 / 6.17	.253 / 6.43
D	.635 / 16.13	.665 / 16.89
E	.555 / 14.10	.565 / 14.35
F	.739 / 18.77	.749 / 19.02
G	.315 / 8.00	.325 / 8.26
H	.002 / 0.05	.006 / 0.15
I	.055 / 1.40	.065 / 1.65
J	.075 / 1.91	.095 / 2.41
K		.190 / 4.83
L	.245 / 6.22	.255 / 6.48
M	.092 / 2.34	

**ORDER CODE: ASI10517**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CB0</sub></b>	I <sub>C</sub> = 3.0 mA	45			<b>V</b>
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 3.0 mA	12			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 3.0 mA	3.5			<b>V</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 600 mA	15		150	<b>---</b>
<b>C<sub>OB</sub></b>	V <sub>CB</sub> = 28 V      f = 1.0 MHz			7.0	<b>pF</b>
<b>P<sub>G</sub></b> <b>η<sub>C</sub></b>	V <sub>CC</sub> = 28 V      P <sub>OUT</sub> = 10 W      f = 1.65 GHz	11 45			<b>dB</b> <b>%</b>